

Product Brief - Preliminary

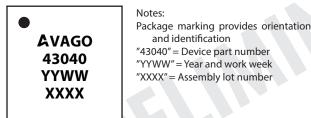
Description

Avago Technologies' MGA-43040 is a fully match amplifier for use in the (2.3-2.4) GHz band. High linear output power at 5V is achieved through the use of A Technologies' proprietary 0.25um GaAs Enhancement pHEMT process. MGA-43040 is housed in a miniature 5.0 5.0mm molded-chip-on-board (MCOB) module package detector is also included on-chip. The compact footprint coupled with high gain, high linearity and good efficiency the MGA-43040 an ideal choice as a power amplifier cell BTS PA applications.

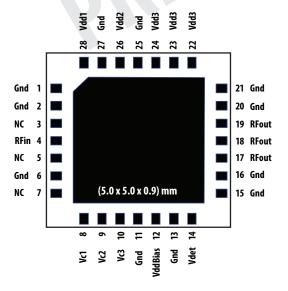
Applications

• Final stage high linearity amplifier Enterprise Femtocell PA targeted for small cell BTS downlink applications

Package Outline (Top View)



Pin Configuration



Features

- High linearity performance Max -48dBc ACPR^[1] at 27.0dBm linear output power (biased with 5 supply)
- High Gain : 42dB
- Good efficiency
- Fully matched
- Built-in detector
- GaAs E-pHEMT Technology^[2]
- Low cost small package size: 5.0 x 5.0 x 0.9 mm

Specifications

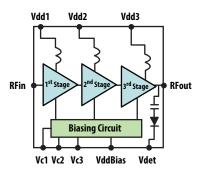
2.35GHz; 5.0V, Idq=350mA (typ), LTE 20MHz 100RB

- PAE:13%
- 27.0dBm linear Pout @ ACPR
- 42dB Gain
- Detector range : 20dB

Notes:

- 1. LTE 20MHz 100RB Test Mode 1.1
- 2. Enhancement mode technology employs positive Vgs, thereby eliminating the need of negative gate voltage associated with conventional depletion mode devices.

Functional Block Diagram





Attention: Observe precautions for handling electrostatic sensitive devices. ESD Machine Model = TBD ESD Human Body Model = TBD Refer to Avago Application Note A004R: Electrostatic Discharge, Damage and Control.

This preliminary data is provided to assist you in the evaluation of product(s) currently under development. Until Avago Technologies releases this product for general sales, Avago Technologies reserves the right to alter prices, specifications, features, capabilities, functions, release dates, and remove availability of the product(s) at anytime.

Absolute Maximum Rating ^[1] $T_A = 25^{\circ} C$

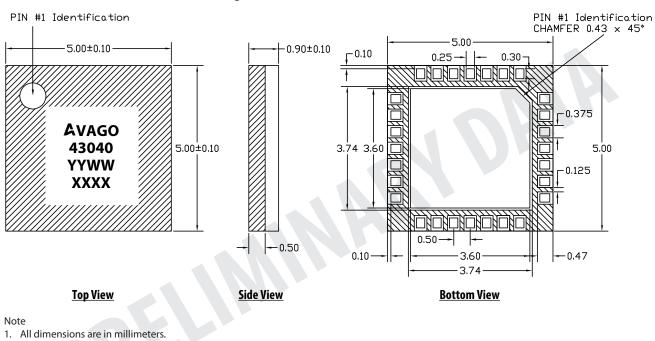
Parameter	Units	Absolute Max.
Supply voltages, bias supply voltage	V	6
Control Voltage	V	(Vdd)
CW RF Input Power	dBm	20
Total Power Dissipation ^[3]	W	TBD
Junction Temperature	°C	150
Storage Temperature	°C	-65 to 150
	Supply voltages, bias supply voltage Control Voltage CW RF Input Power Total Power Dissipation ^[3] Junction Temperature	Supply voltages, bias supply voltageVControl VoltageVCW RF Input PowerdBmTotal Power Dissipation ^[3] WJunction Temperature°C

Thermal Resistance [2,3]

 $\theta_{ic} = 14.2^{\circ}C/W$

Notes:

- 1. Operation of this device in excess of any of these limits may cause permanent damage.
- 2. Thermal resistance measured using Infra-Red Measurement Technique.
- 3. Board temperature (T_B) is 25 °C , for T_B >TBD °C derate the device power at TBD mW per °C rise in Board (package belly) temperature.



2. Dimensions are inclusive of plating.

3. Dimensions are exclusive of mold flash and metal burr.

Part Number Ordering Information

Part Number	Qty	Container
MGA-43040-BLKG	100	Antistatic Bag
MGA-43040-TR1G	1000	7" Reel

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For product information and a complete list of distributors, please go to our web site: www.avagotech.com

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MCOB (5.0 x 5.0 x 0.9) mm 28-Lead Package Dimensions